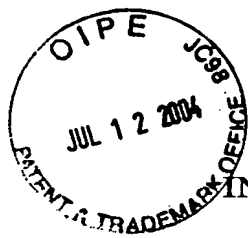


IFW



Docket No.: M4065.0762/P762
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Chandra Mouli

Application No.: 10/681,108

Confirmation No.: 8110

Filed: October 9, 2003

Art Unit: 2811

For: ULTRA-SHALLOW PHOTODIODE
USING INDIUM

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

U.S. Patent and Trademark Office
220 20th Street S.
Customer Window, Mail Stop Amendment
Crystal Plaza Two, Lobby, Room 1B03
Arlington, VA 22202

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed more than three months after the U.S. filing date, but before the mailing date of a first Office Action on the merits.

A copy of each reference on the PTO/SB/08 is attached.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR

1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0762/P762. A duplicate copy of this paper is enclosed.

Dated: July 13, 2004

Respectfully submitted,

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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/681,108-Conf. #8110
				Filing Date	October 9, 2003
				First Named Inventor	Chandra Mouli
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0762/P762

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	AA	P. BOULON et al., "Anomalous Short Channel Effects in Indium Implanted nMOSFETS," 1997 IEEE.	
	AB	Y. LEE et al., "Indium Doped nMSOFETs and Buried Channel pMOSFETs with n+ Polysilicon Gate," Jpn. J. Appl. Phys. Vol. 36 (1997), pp. 1341-1345.	
	AC	I. C. KIZILYALLI et al., "n+ Polysilicon Gate PMOSFET's with Indium Doped Buried-Channels," IEEE Electron Device Letters, Vol. 17 (1996), pp. 46 49.	
	AD	G. G. SHAHIDI, "Indium Channel Implants for Improved MOSFET Behavior at the 100-nm Channel Length Regime," IEEE Transactions on Electronic Devices, Vol. 36 (1989) p. 2605.	
	AE	H. TIAN et al., "A Comparative Study of Indium and Boron Implanted Silicon Bipolar Transistors," IEEE Transactions on Electron Devices, Vol. 48 (2001), pp.2520-2524	

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.